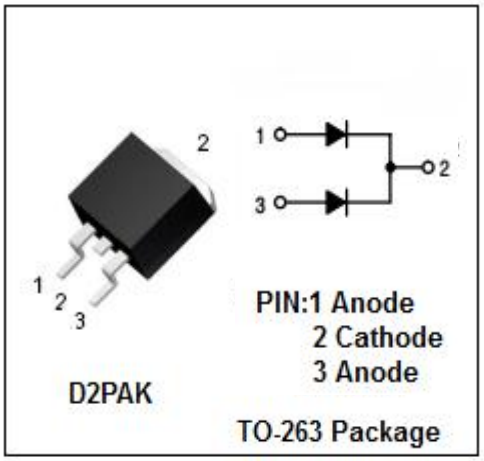
Schottky Barrier Rectifier — RB298NS100

FEATURES

- With TO-263(D2PAK) packaging
- Low leakage current, low power loss, high efficiency
- High frequency operation
- High current capability
- Low stored charge majority carrier conduction
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

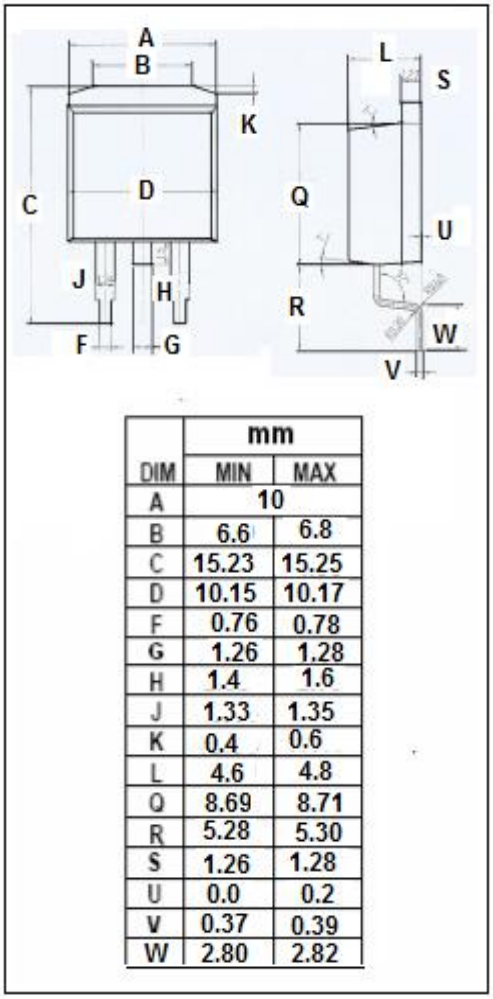


APPLICATIONS

- Switching power supply
- High frequency inverters
- Freewheeling diodes
- Reverse battery protection
- Polarity protection applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{RRM} V_{RMS} V_R	Peak Repetitive Reverse Voltage RMS Voltage DC Blocking Voltage	100	V
$I_{F(AV)}$	Average Rectified Forward Current @Tc=130℃	30	A
$I_{F(RMS)}$	Forward rms current	60	A
I_{FSM}	Nonrepetitive Peak Surge Current (10ms single half sine-wave superimposed on rated load conditions)	100	A
T_J	Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	10	
B	6.6	6.8
C	15.23	15.25
D	10.15	10.17
F	0.76	0.78
G	1.26	1.28
H	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
Q	8.69	8.71
R	5.28	5.30
S	1.26	1.28
U	0.0	0.2
V	0.37	0.39
W	2.80	2.82

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	2.0	℃/W

ELECTRICAL CHARACTERISTICS (Pulse Test: Pulse Width=300 μ s,Duty Cycle≤1%)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Maximum Instantaneous Forward Voltage	I_F= 15A	0.87	V
I_R	Maximum Instantaneous Reverse Current	V_R= rated V_{RRM}; Tc= 25℃	10	mA